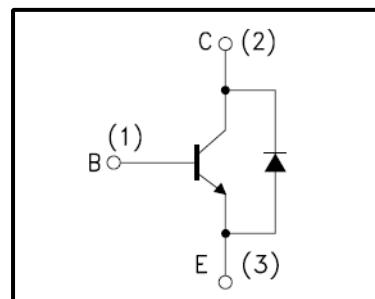


High Voltage Fast-Switching NPN Power Transistor

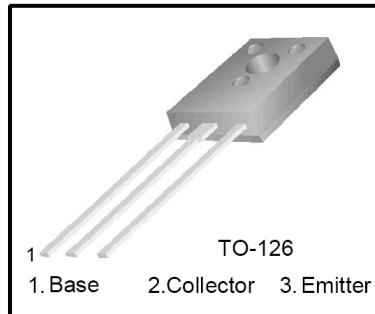
Features

- ◆ Very High Switching Speed
- ◆ High Voltage Capability
- ◆ High Voltage Capability
- ◆ Wide Soa
- ◆ Built-in freewheeling diode



General Description

This Device is designed for high voltage, High speed switching characteristics required such as lighting system, switching mode power supply.



Absolute Maximum Ratings($T_c = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Value	Units
V_{CES}	Collector-Emitter Voltage	$V_{BE} = 0$	400	V
V_{CEO}	Collector-Emitter Voltage	$I_B = 0$	200	V
V_{EBO}	Emitter-Base Voltage	$I_C = 0$	9.0	V
I_C	Collector Current		1.2	A
I_{CP}	Collector pulse Current		3.0	A
P_c	Total Dissipation at $T_c = 25^\circ\text{C}$		10	W
T_J	Operation Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature		- 40 ~ 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance Junction to Case	3.12	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	89	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
BV_{CBO}	Collector-Base Breakdown Voltage	$I_c=0.5\text{mA}, I_e=0$	400			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_c=10\text{mA}, I_b=0$	200	-	-	V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_c=100\text{mA}, I_b=20\text{mA}$	-	-	0.5	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	$I_c=100\text{mA}, I_b=20\text{mA}$	-	-	1.0	V
I_{CBO}	Collector-Base Cutoff Current	$V_{cb}=350\text{V}, I_e=0\text{mA}$	-	-	100	μA
I_{CEO}	Collector-Emitter Cutoff Current	$V_{ce}=200\text{V}, I_b=0\text{mA}$	-	-	200	μA
I_{EBO}	Emitter- Base Cutoff Current	$V_{eb}=9\text{V}, I_c=0\text{mA}$	-	-	20	μA
h_{FE}	DC Current Gain	$V_{ce}=5\text{V}, I_c=200\text{mA}$	10	-	40	
		$V_{ce}=5\text{V}, I_c=1\text{mA}$	8	-	-	
ts tf	Storage Time Fall Time	$V_{cc}=250\text{V}$ $I_c=5 I_B$ $I_{B1}=- I_{B2}=0.04\text{A}$	2	-	4	μs
			-	-	0.8	
VFSD						

Note:

Pulse Test : Pulse width 300, Duty cycle 2%

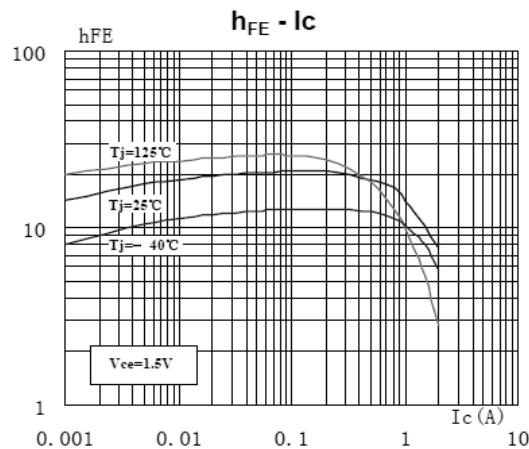


Fig. 1 DC Current Gain

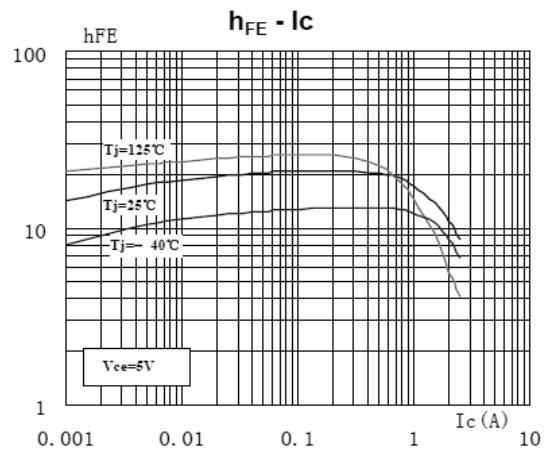


Fig. 2 DC Current Gain

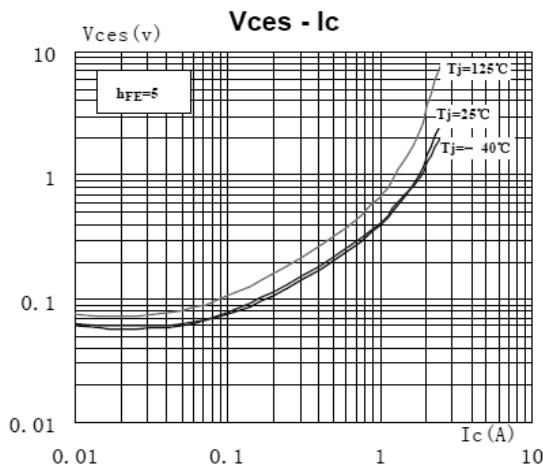


Fig. 3 VCE Saturation Voltage

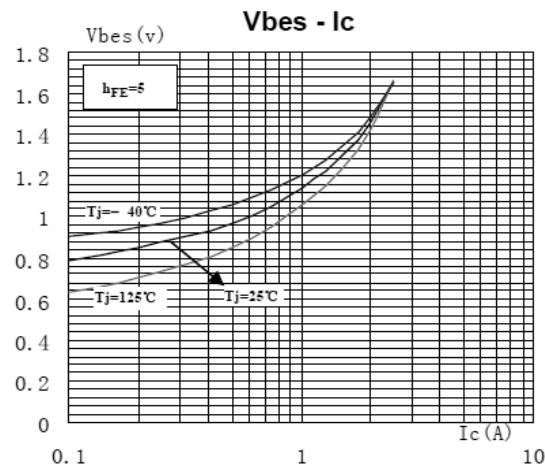


Fig. 4 VBE Saturation Voltage

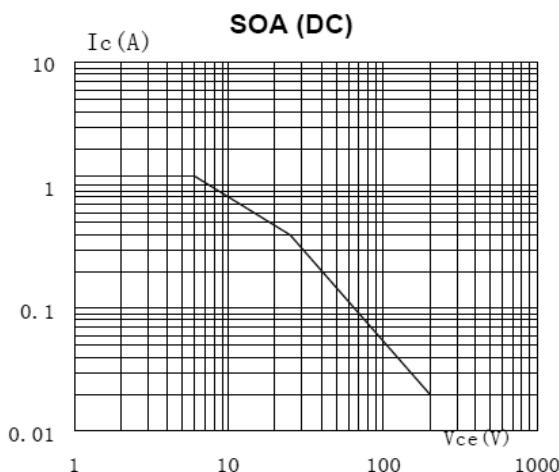


Fig. 5 Safe Operation Area

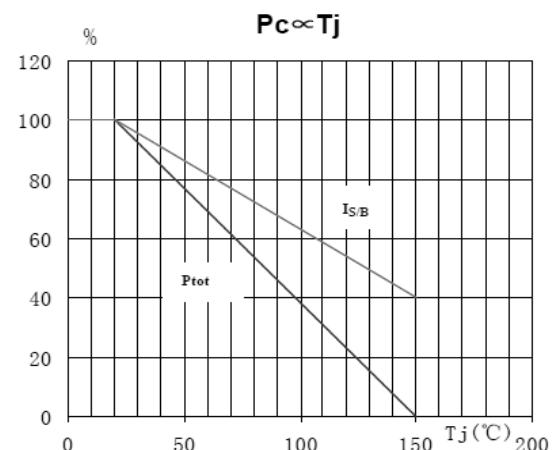


Fig. 6 Power Derating

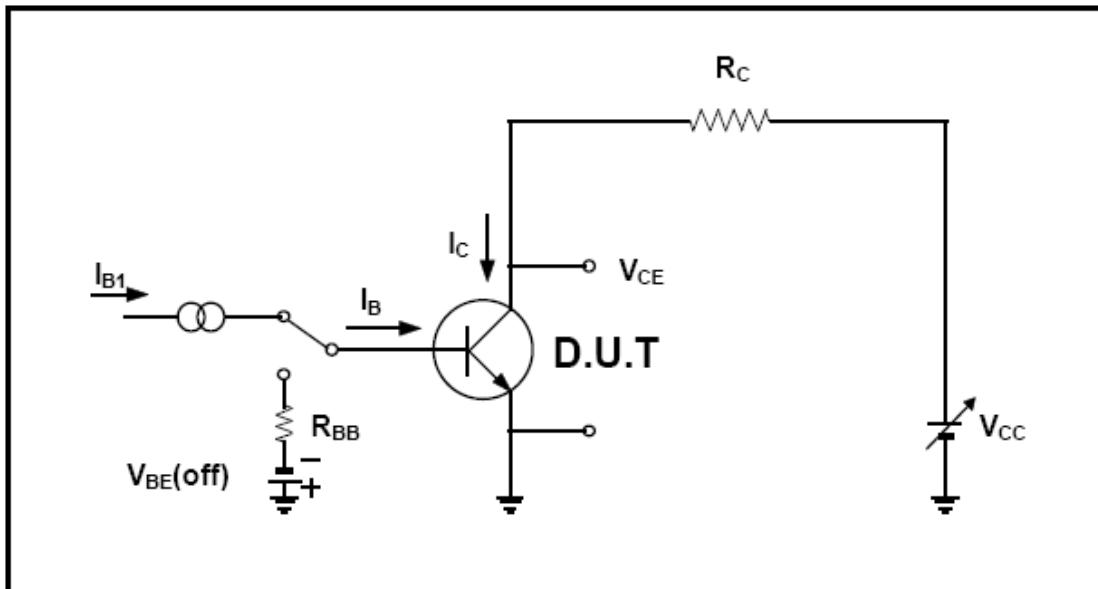


Fig.7 Resistive Load Switching Test Circuit

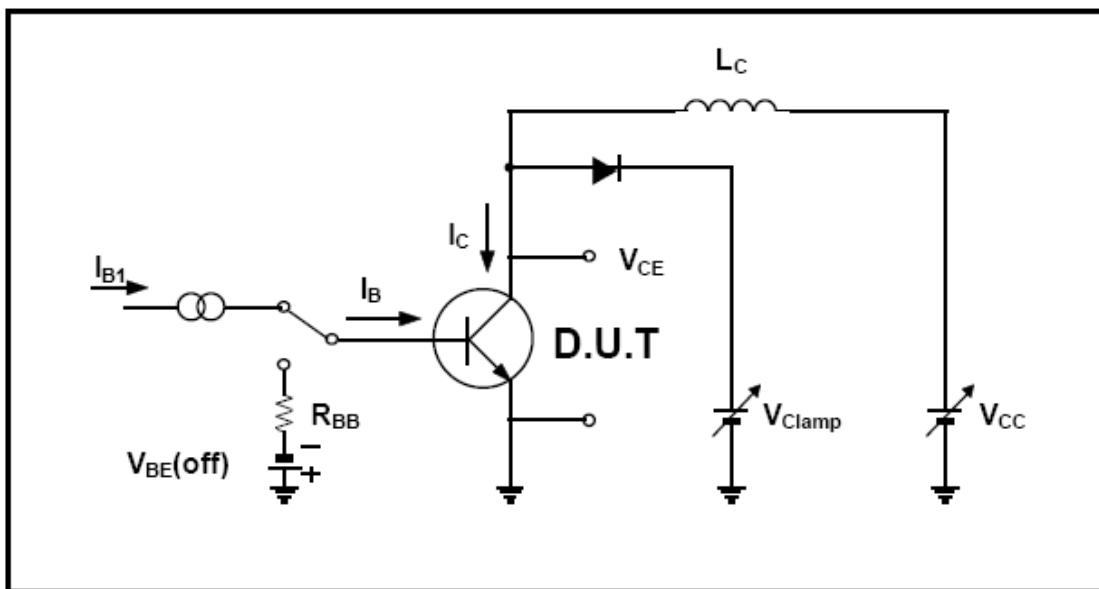


Fig.8 Inductive Load Switching & RBSOA Test Circuit

TO-126 Package Dimension